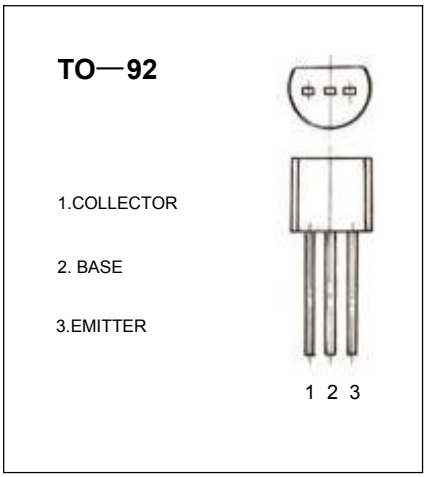
TO-92 Plastic-Encapsulate Transistors

BC556 TRANSISTOR（ NPN ）



FEATURES

Power dissipation

P_{CM}: 0.625 W（Tamb=25℃）

Collector current

I_{CM}: 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 80 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C=0.1μA， I_E=0	-80			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C=2mA， I_B=0	-65			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=100μA， I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-70 V， I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-60 V， I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5 V， I_C=0			-0.1	μA
DC current gain(note)	H_{FE}（1）	V_{CE}=5V, I_C=-2mA	120		800	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-10mA, I_B=-0.5mA			-0.3	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-10mA, I_B=-0.5mA			-0.8	V
Base-emitter voltage	V_{BE}	V_{CE}=5V, I_C=-2mA	0.55		0.7	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA f=-100MHz	150			MHz

CLASSIFICATION OF HFE

Rank	1	2	3
Range	110-220	200-450	420-800